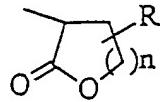


1      WHAT IS CLAIMED IS

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1. An acid-sensitive polymer compound,  
comprising:  
    a film-forming polymer;  
    a carboxyl group bonding to a side chain of  
10     said polymer main chain, said carboxyl group having a  
protective group; and  
    an additional acidic functional group  
bonding to a side chain of said polymer main chain,  
said acidic functional group having an acid-cleavable  
15     protective group;  
    said carboxyl group having, as said  
protective group, a lactone structure represented by a  
formula

20



wherein n is an integer of 1 - 4, and R represents any  
of a hydrogen atom, an alkyl group, an alkoxy group  
25     or an alkoxy carbonyl group and bonding to an arbitrary  
position of said lactone structure excluding a second  
position forming an ester bonding.

30

2. An acid-sensitive polymer compound as  
claimed in claim 1, wherein said lactone part is  
formed of 2-hydroxy- $\tau$ (gamma)-butyrolactone.

35

1       3. An acid-sensitive polymer compound as  
claimed in claim 1, wherein said acid-sensitive  
polymer includes a monomer unit selected from a group  
consisting of acrylate and methacrylate monomer unit,  
5       a vinylphenol monomer unit and an N-substituted  
maleimide monomer unit.

10

4. An acid-sensitive polymer compound as  
claimed in claim 1, wherein said additional acidic  
functional group includes an additional carboxyl group  
having an acid-cleavable protective group, said acid-  
15      cleavable protective group having a formula of

20

wherein  $R_1$  represents an alkyl group having a straight  
chain or a branched chain including 1 - 4 carbon  
atoms, said alkyl group being any of a substituted  
group and an unsubstituted group, and wherein  $Z_1$   
25      represents a plurality of atoms necessary to complete  
an alicyclic hydrocarbon group together with the  
carbon atoms connected to  $R_1$ .

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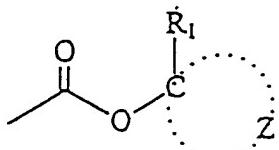
5. An acid-sensitive polymer compound as  
claimed in claim 1, wherein said additional functional  
group includes a monomer unit having an ester group,  
35      said ester group including a polycyclic alicyclic  
hydrocarbon part that causes a deprotection in  
response to an acid produced by a photoacid generator.

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1       6. An acid-sensitive polymer compound as  
claimed in claim 5, wherein said polycyclic alicyclic  
hydrocarbon part includes an adamantyl group or a  
norbornyl group.

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10      7. An acid-sensitive polymer compound as  
claimed in claim 4, wherein said additional carboxyl  
group having a formula of:



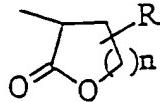
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wherein  $R_1$  represents an alkyl group having a straight chain or a branched chain including 1 - 4 carbon atoms, said alkyl group being any of a substituted group and an unsubstituted group, and wherein  $Z_1$   
20 represents a plurality of atoms necessary to complete an alicyclic hydrocarbon group together with the carbon atoms connected to  $R_1$ .

25

8. A resist composition, comprising:  
an acid-sensitive film-forming polymer  
insoluble to an alkaline solution; a carboxyl group  
30 bonding to a side chain of said polymer's main chain,  
said carboxyl group having a protective group; and an  
additional acidic functional group bonding to a side  
chain of said polymer main chain, said acidic  
functional group having an acid-cleavable protective  
35 group; said carboxyl group having, as said protective  
group, a lactone structure represented by a formula

1



5 wherein n is an integer of 1 - 4, and R represents any of a hydrogen atom, an alkyl group, an alkoxy group or an alkoxy carbonyl group and bonding to an arbitrary position of said lactone structure excluding a second position forming an ester bonding; and

10 a photoacid generator causing a decomposition in response to an absorption of a radiation, said photoacid generator releasing an acid that causes a deprotection of said acid-cleavable protective group in response to said decomposition;

15 said resist composition becoming soluble to said alkaline solution after said acid-cleavable protective group has caused said deprotection.

20

9. A resist composition as claimed in claim 8, wherein said lactone part is formed of 2-hydroxy- $\tau$ (gamma)-butyrolactone.

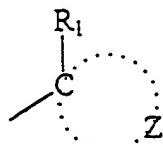
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10. A resist composition as claimed in  
30 claim 8, wherein said acid-sensitive polymer includes a monomer unit selected from a group consisting of acrylate and methacrylate monomer unit, a vinylphenol monomer unit and an N-substituted maleimide monomer unit.

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1        11. A resist composition as claimed in  
claim 8, wherein said additional acidic functional  
group includes an additional carboxyl group having an  
acid-cleavable protective group, said acid-cleavable  
5        protective group having a formula of



10      wherein R<sub>1</sub> represents an alkyl group having a straight  
chain or a branched chain including 1 - 4 carbon  
atoms, said alkyl group being any of a substituted  
group and an unsubstituted group, and wherein Z<sub>1</sub>  
represents a plurality of atoms necessary to complete  
15      an alicyclic hydrocarbon group together with the  
carbon atoms connected to R<sub>1</sub>.

20

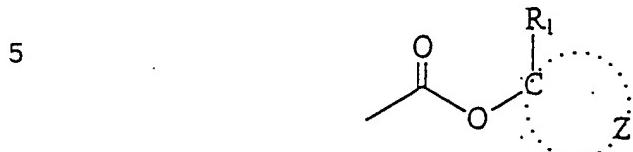
12. A resist composition as claimed in  
claim 8, wherein said additional functional group  
includes a monomer unit having an ester group, said  
ester group including a polycyclic alicyclic  
25      hydrocarbon part that causes a deprotection in  
response to an acid produced by a photoacid generator.

30

13. A resist composition as claimed in  
claim 12, wherein said polycyclic alicyclic  
hydrocarbon part includes an adamantyl group or a  
norbornyl group.

35

1           14. A resist composition as claimed in  
claim 11, wherein said additional carboxyl group  
having a formula of:



wherein  $R_1$  represents an alkyl group having a straight chain or a branched chain including 1 - 4 carbon atoms, said alkyl group being any of a substituted group and an unsubstituted group, and wherein  $Z_1$  represents a plurality of atoms necessary to complete an alicyclic hydrocarbon group together with the carbon atoms connected to  $R_1$ .

20           15. A resist composition as claimed in  
claim 8, wherein said resist composition has an  
absorbance of 1.75 or less when provided on a silicon  
oxide substrate in the form of a resist film.

25

16. A resist composition as claimed in  
claim 8, further comprising a solvent selected from a  
group consisting of: ethyl lactate, methylamylketone,  
methyl-3-methoxypropionate, ethyl-3-ethoxypropionate,  
propyleneglycol methylether acetate, and a mixture  
thereof.

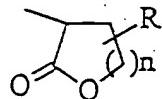
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1           17. A resist composition as claimed in  
claim 16, further including a solvent selected from a  
group consisting of butyl acetate,  $\tau(\gamma)$ -  
butyrolactone and propyleneglycol methylether as an  
5           auxiliary solvent.

10           18. A method of forming a resist pattern,  
comprising the steps of:

               applying a resist composition on a substrate  
to form a resist film, said resist composition  
comprising:

15           an acid-sensitive polymer compound  
insoluble to an alkaline solution, said acid-  
sensitive polymer compound comprising a film-  
forming polymer; a carboxyl group bonding to a  
side chain of said polymer main chain, said  
20           carboxyl group having a protective group; and an  
additional acidic functional group bonding to a  
side chain of said polymer main chain, said  
acidic functional group having an acid-cleavable  
protective group; said carboxyl group having, as  
25           said protective group, a lactone structure  
represented by a formula



30           wherein n is an integer of 1 - 4, and R  
represents any of a hydrogen atom, an alkyl  
group, an alkoxy group and an alkoxy carbonyl  
group and bonding to an arbitrary position of  
35           said lactone structure excluding a second  
position forming an ester bonding; and  
               a photoacid generator causing a

1 decomposition in response to an absorption of a  
radiation, said photoacid generator releasing an  
acid that causes a deprotection of said acid-  
cleavable protective group in response to said  
5 decomposition;

said resist composition becoming  
soluble to said alkaline solution after said  
acid-cleavable protective group has caused said  
deprotection;

10 exposing said resist film to an exposure  
radiation that induces said decomposition in said  
photoacid generator; and

developing said resist film, after said  
process of exposing, by a basic solution.

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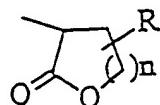
19. A method of forming a resist pattern,  
20 comprising the steps of:

applying a resist composition on a substrate  
to form a resist film, said resist composition  
comprising:

an acid-sensitive polymer compound  
25 insoluble to an alkaline solution, said acid-  
sensitive polymer compound comprising a film-  
forming polymer; a carboxyl group bonding to a  
side chain of said polymer main chain, said  
carboxyl group having a protective group; and an  
30 additional acidic functional group bonding to a  
side chain of said polymer main chain, said  
acidic functional group having an acid-cleavable  
protective group; said carboxyl group having, as  
said protective group, a lactone structure  
35 represented by a formula

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wherein n is an integer of 1 - 4, and R represents any of a hydrogen atom, an alkyl group, an alkoxy group or an alkoxycarbonyl group and connected to an arbitrary position of said lactone structure excluding a second position forming an ester bonding; and

a photoacid generator causing a decomposition in response to an absorption of a radiation, said photoacid generator releasing an acid that causes a deprotection of said acid-cleavable protective group in response to said decomposition;

20 said resist composition becoming  
soluble to said alkaline solution after said  
acid-cleavable protective group has caused said  
deprotection;

exposing said resist film to an exposure radiation that induces said decomposition in said photoacid generator;

25 developing said resist film, after said step  
of exposure, by a basic solution to form a resist  
pattern; and

etching said substrate while using said resist pattern as a mask.

30

20. A method as claimed in claim 19,  
35 wherein said step of forming said resist film includes  
a step of applying a solution of said resist  
composition on said substrate with a thickness of 0.1

1 - 2  $\mu$ m.

5

21. A method as claimed in claim 19,  
wherein said step of exposing said resist film is  
conducted by a KrF excimer laser.

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22. A method as claimed in claim 19,  
wherein said step of exposing said resist film is  
conducted by an ArF excimer laser.

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23. A method as claimed in claim 19,  
wherein said step of developing is conducted by using  
an alkaline aqueous solution.

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